Daniel Becerra

List of Publications by Citations

17 papers	258 citations	10 h-index	16 g-index
17 ext. papers	280 ext. citations	2.5 avg, IF	2.99 L-index

#	Paper	IF	Citations
17	High-power low-droop violet semipolar (303□1□) InGaN/GaN light-emitting diodes with thick active layer design. *Applied Physics Letters*, **2014**, 105, 171106	3.4	50
16	Dynamic characteristics of 410 nm semipolar (202□1□) III-nitride laser diodes with a modulation bandwidth of over 5 GHz. *Applied Physics Letters*, **2016**, 109, 101104	3.4	26
15	High spatial uniformity of photoluminescence spectra in semipolar (202□1) plane InGaN/GaN quantum wells. *Journal of Applied Physics*, **2015**, 117, 023111	2.5	25
14	Demonstration of enhanced continuous-wave operation of blue laser diodes on a semipolar 202□1□ GaN substrate using indium-tin-oxide/thin-p-GaN cladding layers. *Optics Express*, **2018**, 26, 1564-1572	3.3	22
13	Impact of carrier localization on radiative recombination times in semipolar (202□1) plane InGaN/GaN quantum wells. *Applied Physics Letters*, **2015**, 107, 211109	3.4	20
12	Continuous-wave operation of a semipolar InGaN distributed-feedback blue laser diode with a first-order indium tin oxide surface grating. *Optics Letters*, **2019**, 44, 3106-3109	3	19
11	Measurement and analysis of internal loss and injection efficiency for continuous-wave blue semipolar (202□1□) III-nitride laser diodes with chemically assisted ion beam etched facets. *Applied Physics Letters*, **2016**, 108, 091106	3.4	18
10	Chemically assisted ion beam etching of laser diode facets on nonpolar and semipolar orientations of GaN. *Semiconductor Science and Technology*, **2016**, 31, 075008	1.8	13
9	Efficient tunnel junction contacts for high-power semipolar III-nitride edge-emitting laser diodes. *Optics Express*, **2019**, 27, 8327-8334	3.3	12
8	Influence of well width fluctuations on recombination properties in semipolar InGaN quantum wells studied by time- and spatially-resolved near-field photoluminescence. *Optical Materials Express*, **2017**, 7, 3116	2.6	10
7	Continuous-wave operation of a $(20bar{2}bar{1})$ InGaN laser diode with a photoelectrochemically etched current aperture. *Applied Physics Express*, **2015**, 8, 042701	2.4	9
6	Semipolar InGaN blue laser diodes with a low optical loss and a high material gain obtained by suppression of carrier accumulation in the p-waveguide region. *Japanese Journal of Applied Physics*, **2019**, 58, 020902	1.4	9
5	CW operation of high-power blue laser diodes with polished facets on semi-polar GaN substrates. *Electronics Letters*, **2016**, 52, 2003-2005	1.1	7
4	Effects of active region design on gain and carrier injection and transport of CW $(20bar{2}bar{1})$ semipolar InGaN laser diodes. *Applied Physics Express*, **2016**, 9, 092104	2.4	6
3	Compensation effects of high oxygen levels in semipolar AlGaN electron blocking layers and their mitigation via growth optimization. *Journal of Crystal Growth*, **2019**, 507, 118-123	1.6	6
2	Properties of near-field photoluminescence in green emitting single and multiple semipolar (202□1) plane InGaN/GaN quantum wells. *Optical Materials Express*, **2016**, 6, 39	2.6	5
1	Semipolar III-nitride laser diodes for solid-state lighting **2019**,		1